

 $I_{FAV} = 2x 120 A$ 

400 V

45 ns

tentative

HiPerFRED<sup>2</sup>

High Performance Fast Recovery Diode Low Loss and Soft Recovery Parallel legs

Part number

**DPF 240 X 400 NA** 



Backside: isolated

## Applications:

- · Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

# Package:

 $V_{RRM} =$ 

**FL** E72873 • Housing: SOT-227B (minibloc)

- Industry standard outline
- Cu base plate internal DCB isolated
- Isolation Voltage 3000 V
- Epoxy meets UL 94V-0
- RoHS compliant

### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- · Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
- Turn-on loss in the commutating switch

# Ratings

Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RRM</sub>	max. repetitive reverse voltage		T <sub>VJ</sub> = 25°C			400	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 400 V	$T_{VJ} = 25^{\circ}C$			5	μΑ
		V <sub>R</sub> = 400 V	$T_{VJ} = 150$ °C			1	mΑ
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 120 A	$T_{VJ} = 25^{\circ}C$			1.25	V
		$I_F = 240 A$				1.45	V
		I <sub>F</sub> = 120 A	T <sub>VJ</sub> = 150°C			1.06	V
		$I_F = 240 A$				1.31	V
I <sub>FAV</sub>	average forward current	rectangular d = 0.5	$T_{\rm C} = 80^{\circ} C$			120	Α
V <sub>F0</sub>	threshold voltage \( \) \( T_{yy} = 150 \cdot \)C				0.80	V	
r <sub>F</sub>	slope resistance	calculation only				2	mΩ
R <sub>thJC</sub>	thermal resistance junction to case					0.45	K/W
T <sub>VJ</sub>	virtual junction temperature			-40		150	°C
P <sub>tot</sub>	total power dissipation		$T_{c} = 25^{\circ}C$			280	W
I <sub>FSM</sub>	max. forward surge current	t = 10 ms (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			2000	Α
I <sub>RM</sub>	max. reverse recovery current		$T_{VJ} = 25^{\circ}C$		6		Α
		$I_F = 120 \text{ A}; V_R = 240 \text{ V}$	$T_{VJ} = 125$ °C		tbd		Α
t <sub>rr</sub>	reverse recovery time	$-di_F/dt = 200 A/\mu s$	$T_{VJ} = 25^{\circ}C$		45		ns
			$T_{VJ} = 125$ °C		tbd		ns
C¹	junction capacitance	V <sub>R</sub> = 200 V; f = 1 MHz	$T_{VJ} = 25^{\circ}C$		187		pF



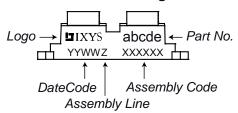
# **DPF 240 X 400 NA**

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Ratings
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Symbol	Definition	Condition	S		min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per termina	al				150	Α
R thCH	thermal resistance case to h	neatsink				0.10		K/W
T <sub>stg</sub>	storage temperature				-40		150	°C
Weight						30		g
M <sub>D</sub>	mounting torque				1.1		1.5	Nm
$M_{T}$	terminal torque				1.1		1.5	Nm
V <sub>ISOL</sub>	isolation voltage	t = 1 second			3000			V
.002		t = 1 minute			2500			V
d <sub>Spp/App</sub>	creepage   striking distance	on surface   through air	terminal to terminal	10.5	3.2			mm
d <sub>Spb/Apb</sub>	creepage   striking distance	on surface   through air	terminal to backside	8.6	6.8			mm

# **Product Marking**



#### Part number

D = Diode

P = HiPerFRED

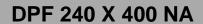
F = ultra fast

240 = Current Rating [A]

X = Parallel legs

400 = Reverse Voltage [V] NA = SOT-227B (minibloc)

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DPF 240 X 400 NA	DPF240X400NA	Tube	10	499554



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